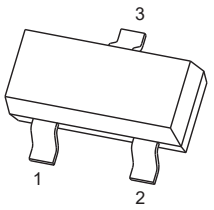
TKMN2312

20V N-Channel MOSFET

Product Summary

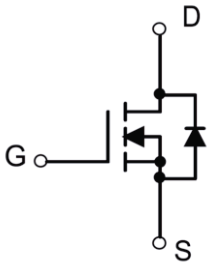
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	17mΩ@4.5V	5 A
	20mΩ@2.5V	
	30mΩ@1.8V	

SOT-23



1. GATE
2. SOURCE
3. DRAIN

Schematic diagram



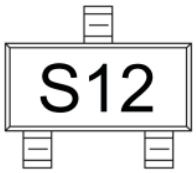
Feature

- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$ and Low Gate Charge

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

MARKING:



ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	20	V
Gate - Source Voltage		V_{GS}	±8	V
Continuous Drain Current[1,5]	T_A = 25℃	I_D	5	A
Pulsed Drain Current[2]		I_{DM}	20	A
Power Dissipation[4,5]	T_A = 25℃	P_D	1.5	W
Thermal Resistance from Junction to Ambient[5]		$R_{\theta JA}$	83.3	℃/W
Junction and Storage Temperature Range		T_J,T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	20			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =20V,V_{GS} = 0V			1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±8V, V_{DS} = 0V			±0.1	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.45	0.7	1.0	V
Drain-source on-resistance[3]	$R_{DS(on)}$	V_{GS} =4.5V, I_D =5.0A		17	24	mΩ
		V_{GS} =2.5V, I_D =4.7A		20	32	
		V_{GS} =1.8V, I_D =4.3A		30	42	
Forward tranconductance[3]	g_{FS}	V_{DS} =10V, I_D =5A	6			S
Dynamic characteristics						
Input Capacitance	C_{iss}	V_{DS} =10V,V_{GS} =0V,f=1MHz		865		pF
Output Capacitance	C_{oss}			105		
Reverse Transfer Capacitance	C_{rss}			55		
Gate resistance	Rg	f =1MHz	0.5		4.8	Ω
Switching Characteristics						
Turn-on delay time	$t_{d(on)}$	V_{GEN}=5V,V_{DD}=10V, I_D =4A,R_G=1Ω, R_L=2.2Ω			10	ns
Turn-on rise time	t_r				20	
Turn-off delay time	$t_{d(off)}$				32	
Turn-off fall time	t_f				12	
Source-Drain Diode characteristics						
Diode Forward voltage[3]	V_{DS}	V_{GS} =0V, I_S=4A		0.75	1.2	V

Notes:

1.The maximum current rating is limited by package.

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

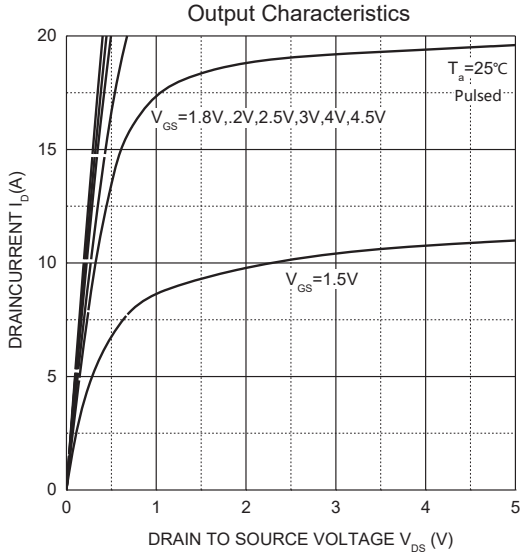
3.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

4.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.

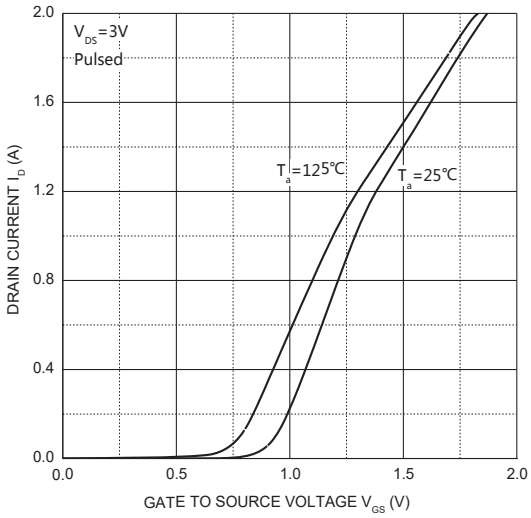
5.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

Typical Electrical and Thermal Characteristics

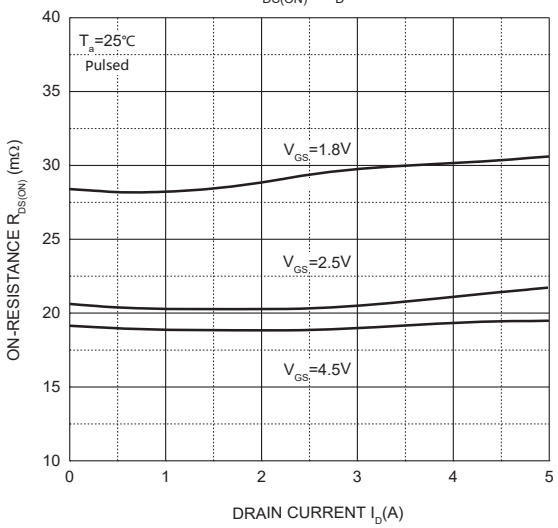
Output Characteristics



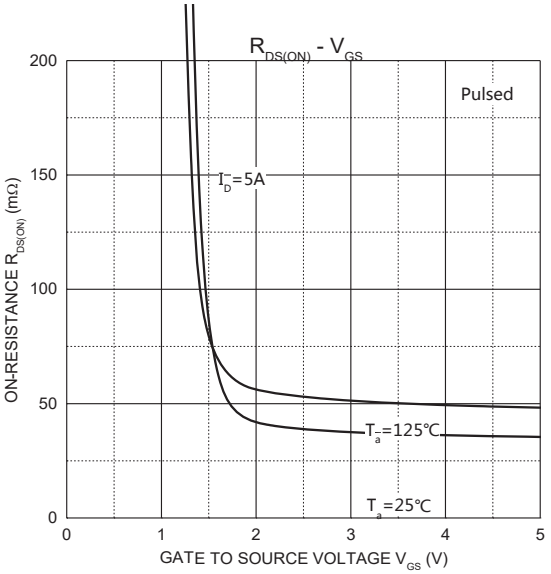
Transfer Characteristics



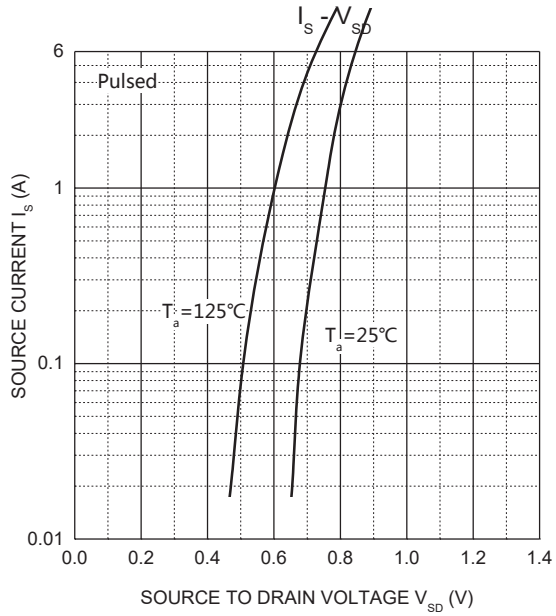
$R_{DS(ON)}$ – I_D



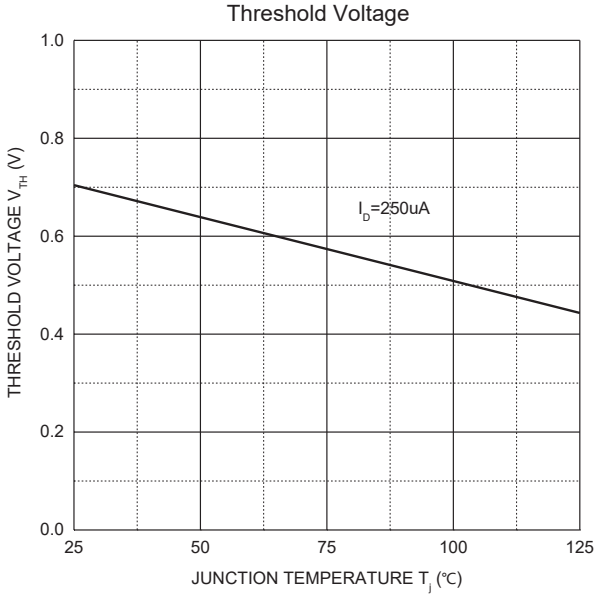
$R_{DS(ON)}$ - V_{GS}

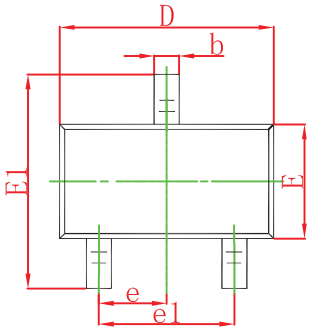


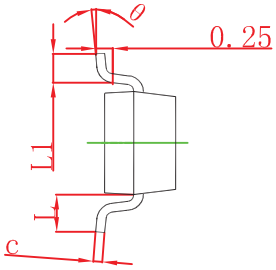
I_S - V_{SD}

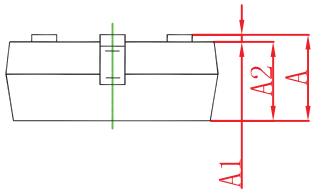


Threshold Voltage



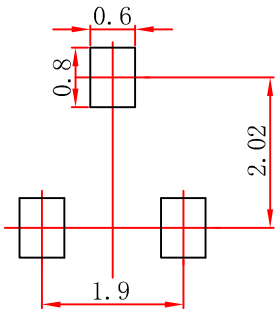






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.